

Maximum Ratings

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current @ $V_{GS} = 10V$	I_D	$T_A = +25^\circ C$ (Note 6)	5.3
		$T_A = +70^\circ C$ (Note 6)	4.2
		$T_A = +25^\circ C$ (Note 5)	3.8
Pulsed Drain Current (Note 7)	I_{DM}	20	A
Continuous Source Current (Body Diode) (Note 6)	I_S	2.1	A
Pulsed Source Current (Body Diode) (Note 7)	I_{SM}	20	A
Power Dissipation at $T_A = +25^\circ C$ (Note 5)	P_D	2	W
Linear Derating Factor		16	mW/ $^\circ C$
Power Dissipation at $T_A = +25^\circ C$ (Note 6)	P_D	3.9	W
Linear Derating Factor		31	mW/ $^\circ C$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ C$

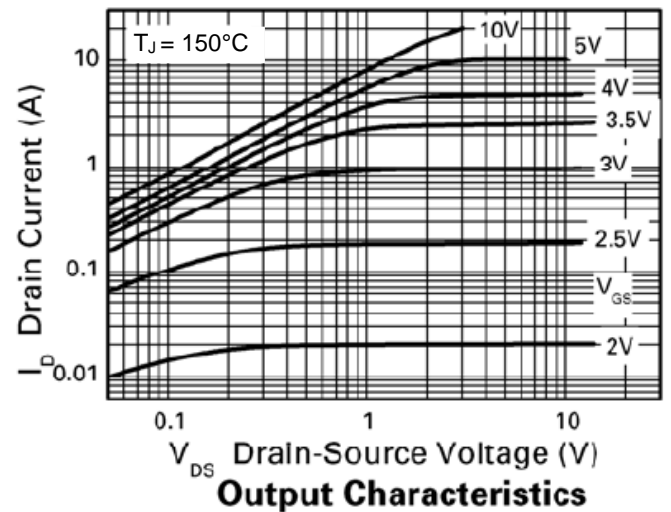
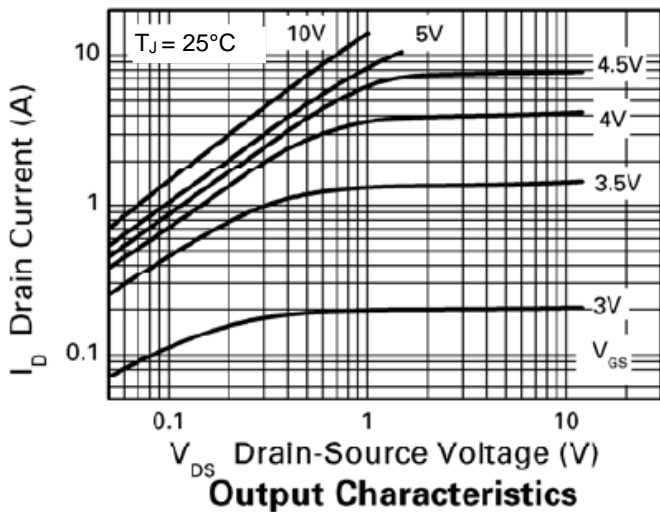
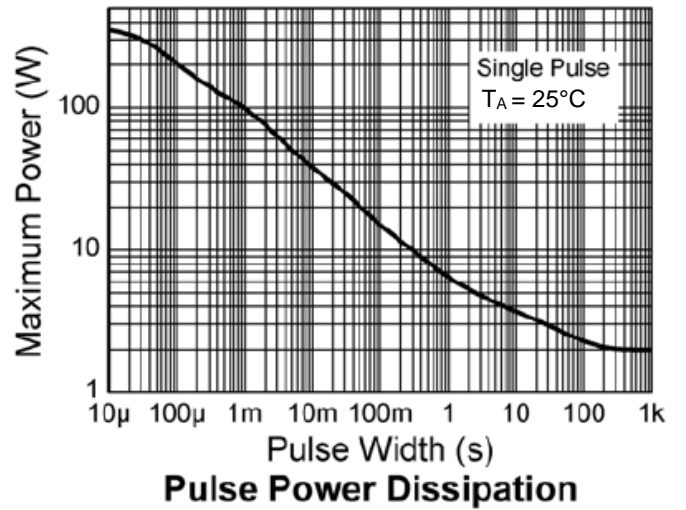
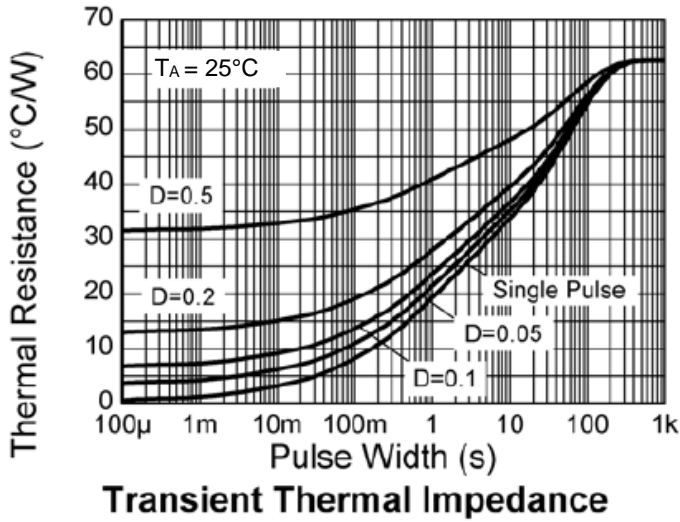
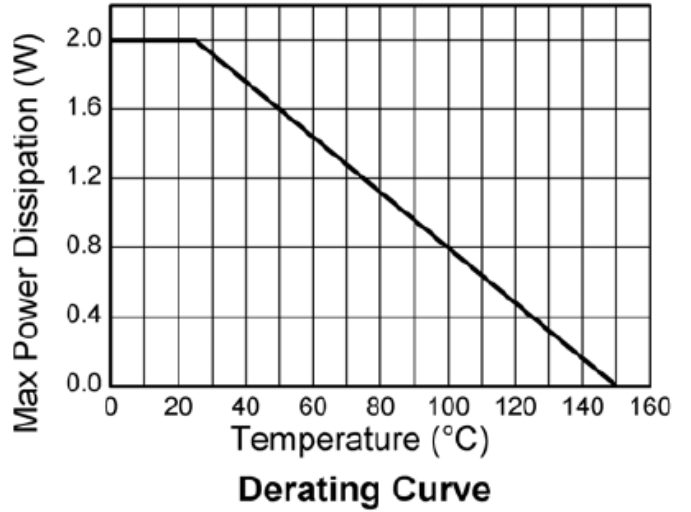
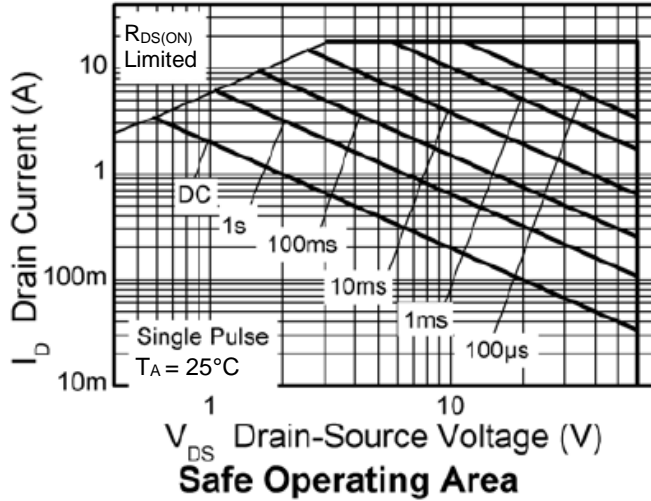
Thermal Characteristics (@ $T_A = +25^\circ C$, unless otherwise specified.)

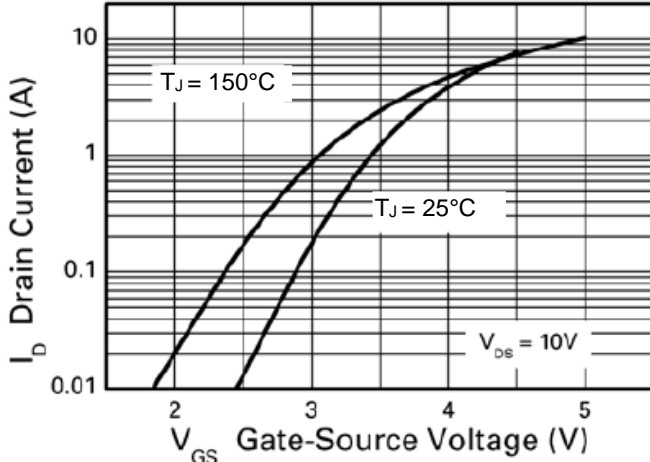
Characteristic	Symbol	Value	Unit
Junction to Ambient (Note 5)	$R_{\theta JA}$	62.5	$^\circ C/W$
Junction to Ambient (Note 6)	$R_{\theta JA}$	32	$^\circ C/W$

Electrical Characteristics (@ $T_A = +25^\circ C$, unless otherwise specified.)

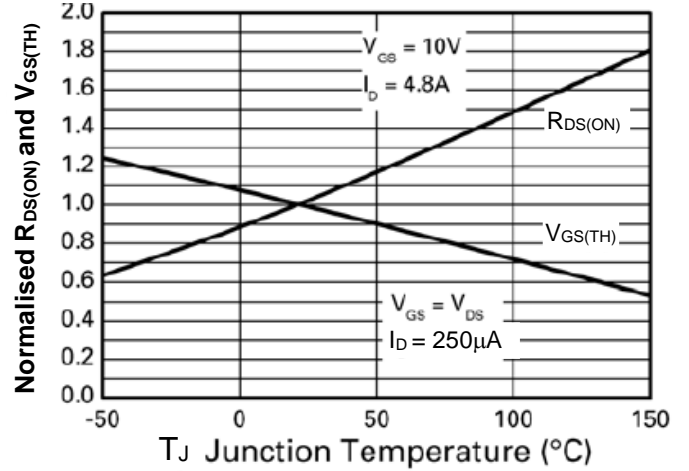
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	0.5	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	—	—	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	—	0.06	0.08	Ω	$V_{GS} = 10V, I_D = 4.8A$
		—	0.08	0.15	Ω	$V_{GS} = 4.5V, I_D = 4.2A$
Forward Transconductance (Note 9)	g_{fs}	—	6.6	—	S	$V_{DS} = 15V, I_D = 4.8A$
Diode Forward Voltage	V_{SD}	—	0.88	1.2	V	$T_J = +25^\circ C, I_S = 4A, V_{GS} = 0V$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	459	—	pF	$V_{DS} = 40V, V_{GS} = 0V, f = 1MHz$
Output Capacitance	C_{oss}	—	44.2	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	24.1	—	pF	
Turn-On Delay Time (Note 8)	$t_{D(ON)}$	—	2.6	—	ns	$V_{DD} = 30V, I_D = 1.5A, R_G \approx 6.0\Omega, V_{GS} = 10V$
Turn-On Rise Time (Note 8)	t_R	—	2.1	—	ns	
Turn-Off Delay Time (Note 8)	$t_{D(OFF)}$	—	12.3	—	ns	
Turn-Off Fall Time (Note 8)	t_F	—	4.6	—	ns	
Gate Charge (Note 8)	Q_G	—	4.0	—	nC	$V_{DS} = 30V, V_{GS} = 5V, I_D = 1.4A$
Total Gate Charge (Note 8)	Q_G	—	5.8	—	nC	$V_{DS} = 30V, V_{GS} = 10V, I_D = 1.4A$
Gate-Source Charge (Note 8)	Q_{GS}	—	1.4	—	nC	
Gate Drain Charge (Note 8)	Q_{GD}	—	1.9	—	nC	
SOURCE-DRAIN DIODE						
Reverse Recovery Time (Note 9)	t_{RR}	—	19.2	—	ns	$T_J = +25^\circ C, I_S = 1.4A, di/dt = 100A/\mu s$
Reverse Recovery Charge (Note 9)	Q_{RR}	—	30.3	—	nC	

- Notes:
5. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.
 6. For a device surface mounted on FR-4 PCB measured at $t < 10s$.
 7. Repetitive rating - 25mm x 25mm FR-4 PCB, $D = 0.02$, pulse width 300 μs - pulse width limited by maximum junction temperature.
 8. Switching characteristics are independent of operating junction temperature.
 9. For design aid only, not subject to production testing.

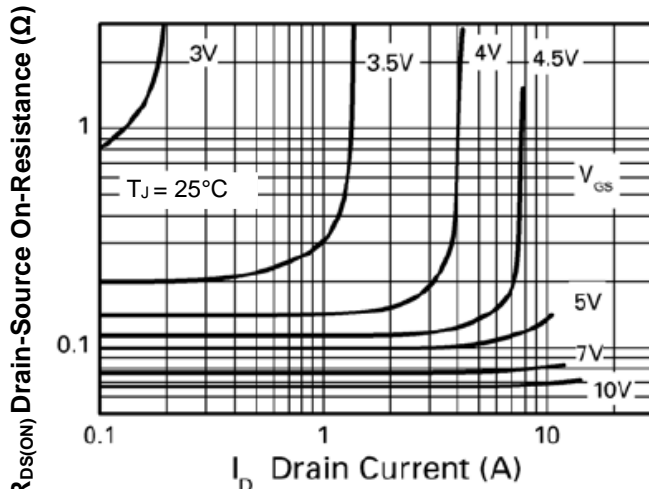




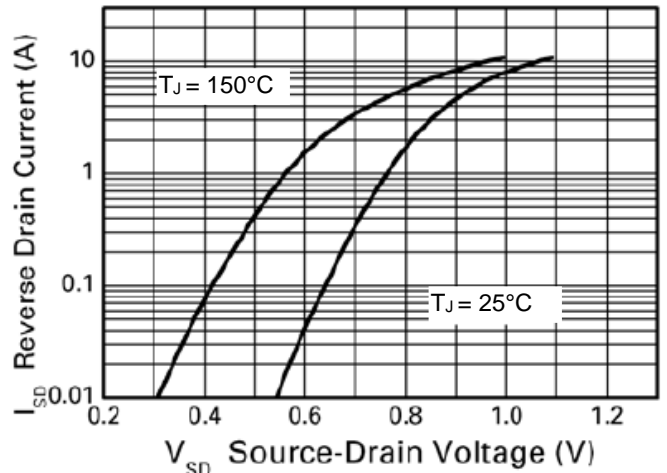
Typical Transfer Characteristics



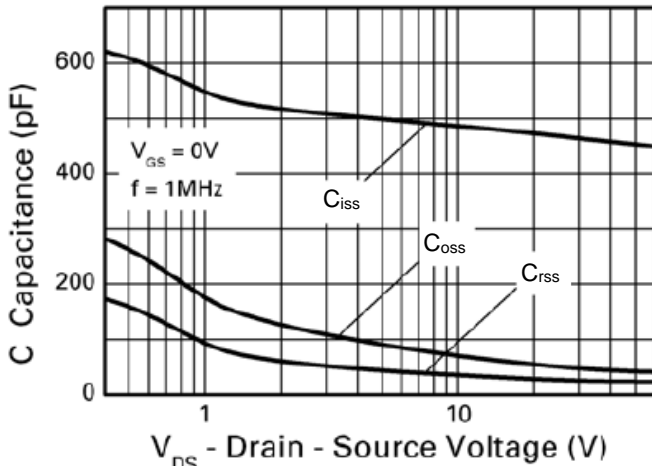
Normalised Curves v Temperature



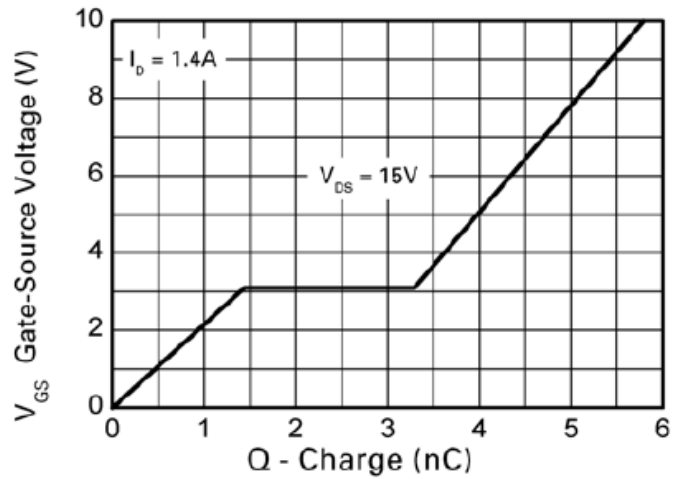
On-Resistance v Drain Current



Source-Drain Diode Forward Voltage

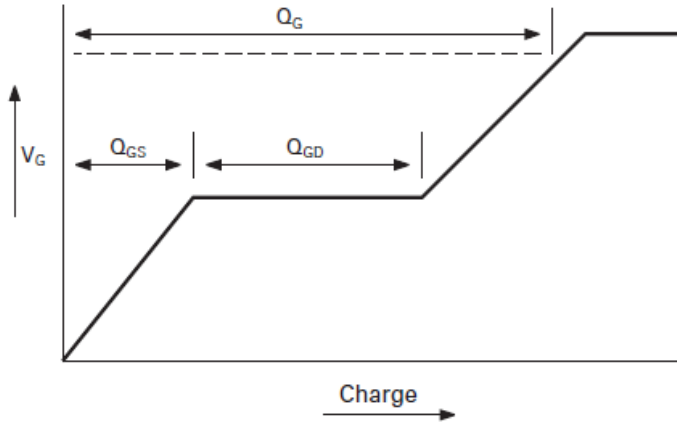


Capacitance v Drain-Source Voltage

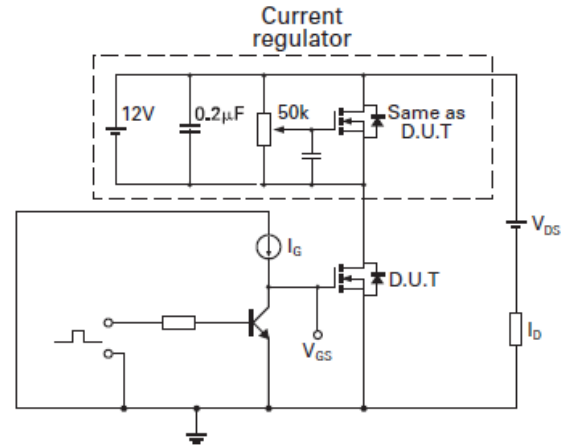


Gate-Source Voltage v Gate Charge

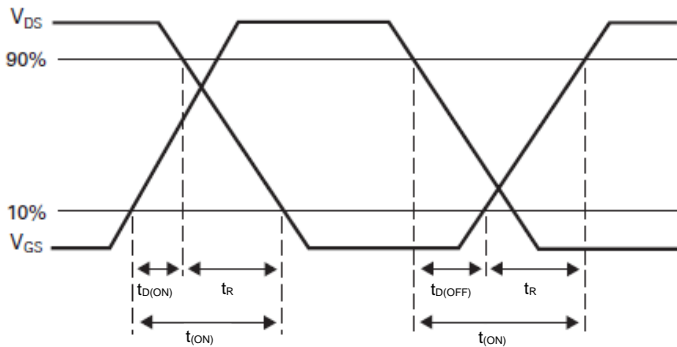
Test Circuits



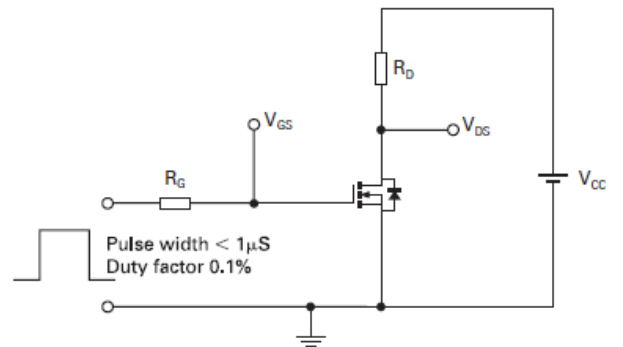
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

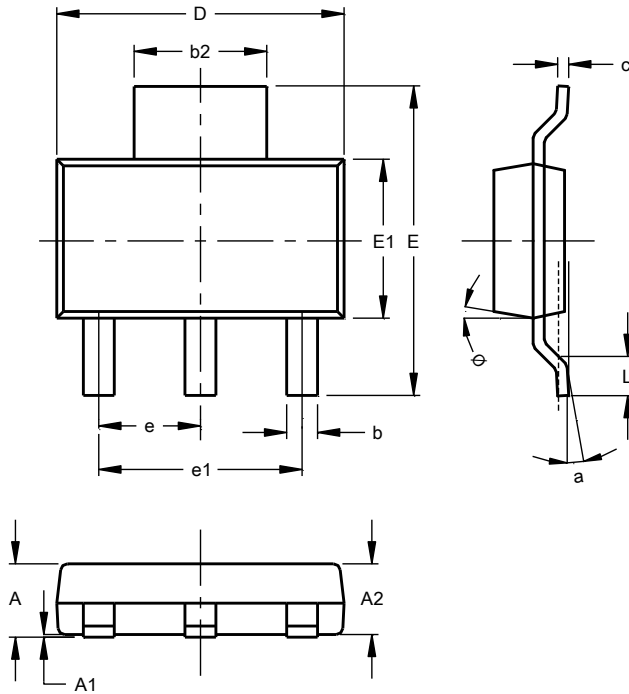


Switching time test circuit

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223 (Type ZN)

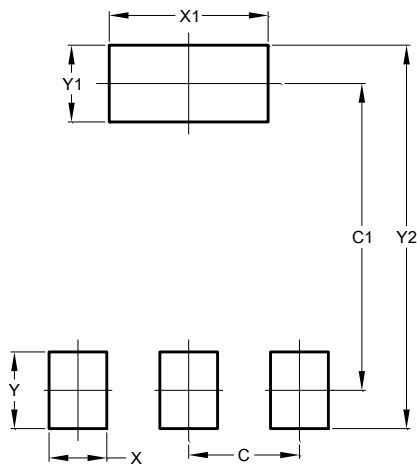


SOT223 (Type ZN)			
Dim	Min	Max	Typ
A	--	1.70	--
A1	0.02	0.10	--
A2	1.50	1.68	1.60
b	0.60	0.80	--
b2	2.90	3.10	--
c	0.24	0.32	--
D	6.30	6.70	--
E	6.70	7.30	--
E1	3.30	3.70	--
e	2.30 NOM		
e1	4.60 NOM		
L	0.90	--	--
a	--	--	10°
θ	--	15°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223 (Type ZN)



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

A. Life support devices or systems are devices or systems which:

1. are intended to implant into the body, or
2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2020, Diodes Incorporated

www.diodes.com

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[Diodes Incorporated:](#)

[ZXMN6A08GQTA](#) [ZXMN6A08GQTC](#)